Abstracts

Microwave Wide-Band Model of GaAs Dual Gate MESFET's

C. Tsironis and R. Meierer. "Microwave Wide-Band Model of GaAs Dual Gate MESFET's." 1982 Transactions on Microwave Theory and Techniques 30.3 (Mar. 1982 [T-MTT]): 243-251.

A multioctave model of GaAs dual gate MESFET’s is presented. It consists of 28 frequency independent elements and is valid between 2 and 11 GHz. Dual gate FET’s with and without intergate ohmic contact have been considered. The modeling method utilized consists in separate dc and HF characterization and equivalent circuit determination of the active device parts in their actual bias conditions. Thereby, two goals are obtained: a) The topology of the overall model can be derived from well-known simpler, partial ones; and b) the starting values of optimization are precise enough to allow reliable physical solutions.

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